Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

H1423

■ GENERAL PURPOSE AMPLIFIER AND LOW NOISE AMPLIFIER APPLICATIONS

■ ABSOLUTE MAXIMUM RATINGS（T_a=25℃）

T_{stg}——Storage Temperature…… -55~150℃

T_j——Junction Temperature……150℃

P_C——Collector Dissipation……625mW

V_{CBO}——Collector-Base Voltage……-40V

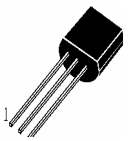
V_{CEO}——Collector-Emitter Voltage……-40V

V_{EBO}——Emitter-Base Voltage……-7V

I_C——Collector Current……-200mA

I_B——Base Current……-200mA

TO-92



1－Emitter，E
2－Base，B
3－Collector，C

■ ELECTRICAL CHARACTERISTICS（T_a=25℃）

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CEO}	Collector-Emitter Breakdown Voltage	−40			V	I_C=-1mA, I_B=0
I_{CBO}	Collector Cut-off Current			−50	nA	V_{CB}=-30V, I_E=0
I_{EBO}	Emitter Cut-off Current			−100	nA	V_{EB}=-6V, I_C=0
H_{FE}	DC Current Gain	70		400		V_{CE}=-5V, I_C=-2mA
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			−0. 22	V	I_C=-50mA, I_B=-10mA
V_{BE}	Base-Emitter Voltage		−0. 65		V	V_{CE}=-5V, I_C=-2mA
f_T	Current Gain-Bandwidth Product	150	300		MHz	V_{CE}=-5V, I_C=-10mA
Cob	Output Capacitance			4. 5	pF	V_{CB}=-10V, I_E=0， f=1MHz